EPIGAP Optronic GmbH
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70

Data Sheet

LED Chip deep red EOLC-660-15

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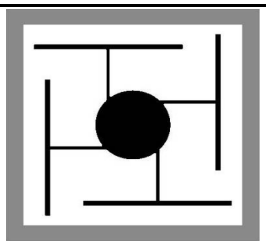
Radiation	Type	Electrodes
deep red	AlGaAs	n (cathode) up



- High luminous intensity
- Thin film structure

- Typ. chip size 340 ± 25 µm
- Typ. thickness 225 ±25 µm

Absolute Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Typ	Unit
Forward DC current	I_F	≤70	mA
Reverse voltage	V_R	≤10	V
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40 ~ +85	°C

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=10 µA	V_F	1.3			V
Forward voltage	I_F=20 mA	V_F		2.1	2.5	V
Reverse current	V_R = 10V	I_R			5	µA
Output power	I_F=20 mA	I_V		9		mW
Peak wavelength	I_F=20 mA	λ_p	650	660	670	nm
Spectral bandwidth at 50%	I_F=20 mA	$\Delta\lambda_{0.5}$		20		nm